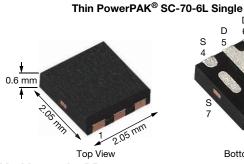
SiA429DJT

Vishay Siliconix

www.vishay.com

P-Channel 20 V (D-S) MOSFET





Bottom View

Marking code: BP

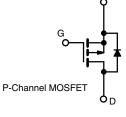
| PRODUCT SUMMARY | | | | | | | | | |
|---|--------|--|--|--|--|--|--|--|--|
| V _{DS} (V) | -20 | | | | | | | | |
| $R_{DS(on)}$ max. (Ω) at V_{GS} = -4.5 V | 0.0205 | | | | | | | | |
| $R_{DS(on)}$ max. (Ω) at V_{GS} = -2.5 V | 0.0270 | | | | | | | | |
| $R_{DS(on)}$ max. (Ω) at V_{GS} = -1.8 V | 0.0360 | | | | | | | | |
| $R_{DS(on)}$ max. (Ω) at V_{GS} = -1.5 V | 0.0600 | | | | | | | | |
| Q _g typ. (nC) | 24.5 | | | | | | | | |
| I _D (A) ^a | -12 | | | | | | | | |
| Configuration | Single | | | | | | | | |

FEATURES

- TrenchFET[®] power MOSFET
- New thermally enhanced PowerPAK[®] SC-70 package
- Small footprint area
- Ultra-thin 0.6 mm height
- Low on-resistance
- 100 % R_a tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · Load switch and charger switch for portable devices
- DC/DC converter



| ORDERING INFORMATION | |
|---------------------------------|---------------------|
| Package | Thin PowerPAK SC-70 |
| Lead (Pb)-free and halogen-free | SiA429DJT-T1-GE3 |

| PARAMETER | | SYMBOL | LIMIT | UNIT | |
|--|------------------------|-----------------------------------|-----------------------|------|--|
| Drain-source voltage | | V _{DS} | -20 | V | |
| Gate-source voltage | | V _{GS} | ± 8 | V | |
| Continuous drain current (T _J = 150 °C) | T _C = 25 °C | | -12 ^a | | |
| | T _C = 70 °C | | -12 ^a | | |
| | T _A = 25 °C | I _D | -10.6 ^{b, c} | | |
| | T _A = 70 °C | | -8.5 ^{b, c} | A | |
| Pulsed drain current (t = 300 µs) | | I _{DM} | -30 | | |
| Continuous source-drain diode current | T _C = 25 °C | | -12 ^a | | |
| | T _A = 25 °C | I _S | -2.9 ^{b, c} | | |
| | T _C = 25 °C | | 19 | | |
| Maximum namer dissinction | T _C = 70 °C | | 12 | w | |
| Maximum power dissipation | T _A = 25 °C | PD | 3.5 ^{b, c} | vv | |
| | T _A = 70 °C | | 2.2 ^{b, c} | | |
| Operating junction and storage temperature ra | nge | T _J , T _{stq} | -55 to +150 | | |
| Soldering recommendations (peak temperature | e) ^{d, e} | | 260 | | |

THERMAL RESISTANCE RATINGS

| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT | |
|----------------------------------|--------------|-------------------|---------|---------|-------|--|
| Maximum junction-to-ambient b, f | t ≤ 5 s | R _{thJA} | 28 | 36 | °C AN | |
| Maximum junction-to-case (drain) | Steady state | R _{thJC} | 5.3 | 6.5 | °C/W | |

Notes

a. Package limited

b. Surface mounted on 1" x 1" FR4 board

t = 5 s c.

- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components f. Maximum under steady state conditions is 80 °C/W

S11-0649-Rev. B, 11-Apr-11

1

Document Number: 67038

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| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|----------------------------------|--|------|--------|--------|----------------|
| Static | | | | • | | |
| Drain-source breakdown voltage | V _{DS} | $V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$ | | - | - | V |
| V _{DS} temperature coefficient | $\Delta V_{DS}/T_{J}$ | L 050 A | - | -12 | - | mV/°C |
| V _{GS(th)} temperature coefficient | $\Delta V_{GS(th)}/T_J$ | I _D = -250 μΑ | - | 2.7 | - | |
| Gate-source threshold voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$ | -0.4 | - | -1 | V |
| Gate-source leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$ | - | - | ± 100 | nA |
| Zara acta veltara ducin ovurant | | $V_{DS} = -20 V, V_{GS} = 0 V$ | - | - | -1 | |
| Zero gate voltage drain current | IDSS | V_{DS} = -20 V, V_{GS} = 0 V, T_{J} = 55 °C | - | - | -10 | μA |
| On-state drain current ^a | I _{D(on)} | $V_{DS} \leq$ -5 V, V_{GS} = -4.5 V | -20 | - | - | А |
| | | $V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -6 \text{ A}$ | - | 0.0170 | 0.0205 | |
| Drain-source on-state resistance ^a | | $V_{GS} = -2.5 \text{ V}, I_D = -2 \text{ A}$ | - | 0.0220 | 0.0270 | |
| | R _{DS(on)} | $V_{GS} = -1.8 \text{ V}, I_D = -2 \text{ A}$ | - | 0.0290 | 0.0360 | Ω |
| | | V _{GS} = -1.5 V, I _D = -1 A | - | 0.0380 | 0.0600 | |
| Forward transconductance ^a | g _{fs} | $V_{DS} = -10 \text{ V}, \text{ I}_{D} = -6 \text{ A}$ | - | 30 | - | S |
| Dynamic ^b | | | | • | | • |
| Input capacitance | C _{iss} | | - | 1750 | - | pF |
| Output capacitance | C _{oss} | V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz | - | 270 | - | |
| Reverse transfer capacitance | C _{rss} | | - | 240 | - | |
| Tatal asta abauna | Qg | $V_{DS} = -10 \text{ V}, V_{GS} = -8 \text{ V}, I_D = -10 \text{ A}$ | - | 41 | 62 | nC |
| Total gate charge | | | - | 24.5 | 37 | |
| Gate-source charge | Q _{gs} | V_{DS} = -10 V, V_{GS} = -4.5 V, I_{D} = -10 A | - | 2.4 | - | |
| Gate-drain charge | Q _{gd} | | - | 6.7 | - | |
| Gate resistance | Rg | f = 1 MHz | 1.3 | 6.3 | 13 | Ω |
| Turn-on delay time | on delay time t _{d(on)} | | - | 22 | 35 | - |
| Rise time | | | - | 25 | 40 | |
| Turn-off delay time | t _{d(off)} | $I_D \cong -8.5$ Å, $V_{GEN} = -4.5$ V, $R_g = 1 \ \Omega$ | - | 70 | 105 | 1 |
| Fall time | t _f | | - | 25 | 40 | |
| Turn-on delay time | t _{d(on)} | | - | 10 | 15 | - ns - - |
| Rise time | t _r | $V_{DD} = -10 \text{ V}, \text{ R}_{\text{I}} = 1.2 \Omega$ | | 10 | 15 | |
| Turn-off delay time | t _{d(off)} | $I_D \cong -8.5$ A, $V_{GEN} = -8$ V, $R_g = 1$ Ω | - | 80 | 120 | |
| Fall time | t _f | | - | 25 | 40 | |
| Drain-Source Body Diode Characteris | tics | | | • | | |
| Continuous source-drain diode current | I _S | T _C = 25 °C | - | - | -12 | |
| Pulse diode forward current | I _{SM} | | - | - | -30 | A |
| Body diode voltage | V _{SD} | I _S = -8.5 A, V _{GS} = 0 V | - | -0.8 | -1.2 | V |
| Body diode reverse recovery time | t _{rr} | · • • | - | 35 | 60 | ns |
| Body diode reverse recovery charge | Q _{rr} | I _F = -8.5 A, di/dt = 100 A/μs, | - | 18 | 30 | nC |
| Reverse recovery fall time | t _a | | | 13 | - | |
| Reverse recovery rise time | t _b | | - | 22 | _ | ns |

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2\%$

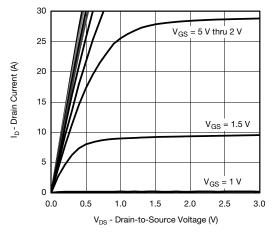
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

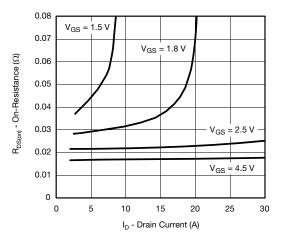
2



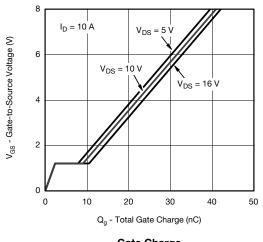
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



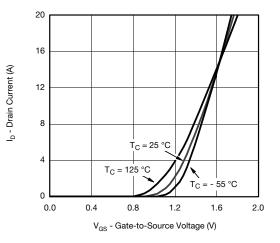
Output Characteristics



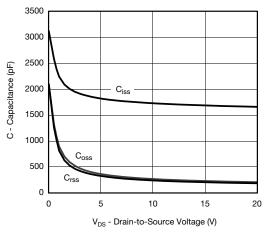
On-Resistance vs. Drain Current and Gate Voltage



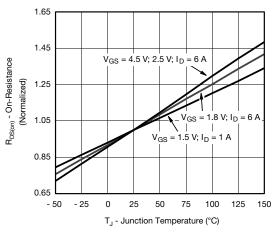




Transfer Characteristics



Capacitance



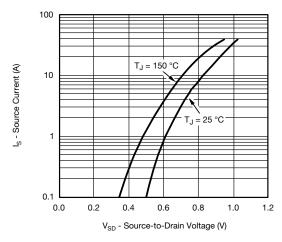
On-Resistance vs. Junction Temperature

3

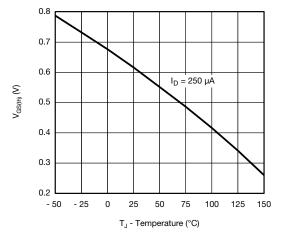
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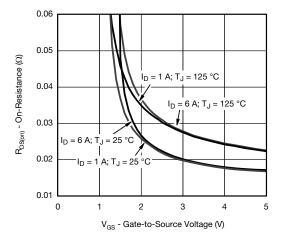
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



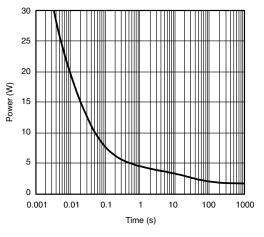
Source-Drain Diode Forward Voltage



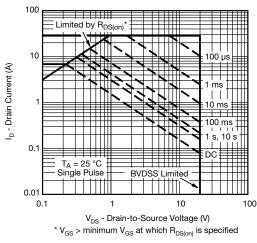




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

4

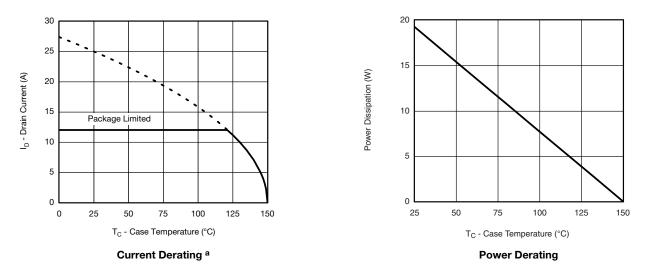
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

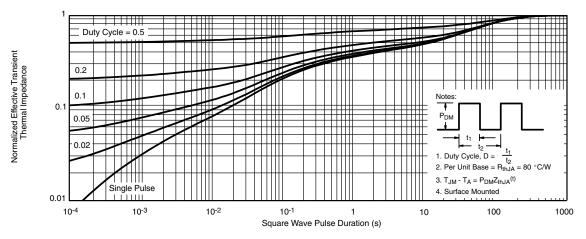


Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

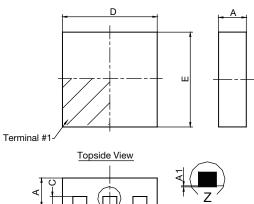


Normalized Thermal Transient Impedance, Junction-to-Case

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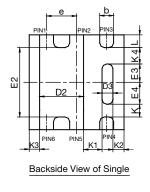


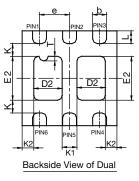
Case Outline for PowerPAK® SC70T



Side View







| | SINGLE PAD | | | | | DUAL PAD | | | | | | | |
|--|-------------|------------|-------|------------|------------|-------------|------------|------------|--------|------------|------------|-------|--|
| DIM. | MILLIMETERS | | | INCHES | | MILLIMETERS | | | INCHES | | | | |
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | |
| Α | 0.525 | 0.60 | 0.65 | 0.0206 | 0.024 | 0.026 | 0.525 | 0.60 | 0.65 | 0.0206 | 0.024 | 0.026 | |
| A1 | 0 | - | 0.05 | 0 | - | 0.002 | 0 | - | 0.05 | 0 | - | 0.002 | |
| b | 0.23 | 0.30 | 0.38 | 0.009 | 0.012 | 0.015 | 0.23 | 0.30 | 0.38 | 0.009 | 0.012 | 0.015 | |
| С | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | |
| D | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | |
| D2 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 | 0.513 | 0.613 | 0.713 | 0.020 | 0.024 | 0.028 | |
| D3 | 0.135 | 0.235 | 0.335 | 0.005 | 0.009 | 0.013 | | | | | | | |
| E | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | |
| E2 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 | |
| E3 | 0.345 | 0.395 | 0.445 | 0.014 | 0.016 | 0.018 | | | | | | | |
| E4 | 0.425 | 0.475 | 0.525 | 0.017 | 0.019 | 0.021 | | | | | | | |
| е | | 0.65 BSC | | 0.026 BSC | | | 0.65 BSC | | | 0.026 BSC | | | |
| К | | 0.275 TYP. | | | 0.011 TYP. | | | 0.275 TYP. | | | 0.011 TYP. | | |
| K1 | | 0.400 TYP. | | | 0.016 TYP. | | | 0.320 TYP. | | | 0.013 TYP. | | |
| K2 | 0.240 TYP. | | | 0.009 TYP. | | | 0.252 TYP. | | | 0.010 TYP. | | | |
| K3 | 0.225 TYP. | | | | 0.009 TYP. | | | | | | | | |
| K4 | 0.355 TYP. | | | 0.014 TYP. | | | | | | | | | |
| L | 0.175 | 0.275 | 0.375 | 0.007 | 0.011 | 0.015 | 0.175 | 0.275 | 0.375 | 0.007 | 0.011 | 0.015 | |
| Т | | | | | | | 0.05 | 0.10 | 0.15 | 0.002 | 0.004 | 0.006 | |
| ECN: C12-0160-Rev. B, 05-Mar-12 DWG: 5994 | | | | | | | | | | | | | |

Notes

1. All dimensions are in millimeter. Millimeters will govern.

2. Package outline exculsive of mold flash and metal burr.

3. Package outline inclusive of plating



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